

<p>Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE</p> <p><b>LIST OF REFERENCES CITED BY APPLICANT</b></p> <p>(Use several sheets if necessary)</p> <p><i>DEC 9 2005</i></p> <p><i>CANCELLED</i></p>		<p>Atty. Docket No. YOR920030334US1 (16899)</p> <p>Applicant: Ricky S. Amos et al.</p> <p>Filing Date: February 25, 2004</p>	<p>Serial No. 10/786,901</p> <p>Group Art Unit 2891</p>
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## **U.S. PATENT DOCUMENTS**

EXAMINE R INITIAL*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
AKS	4,780,429	10/25/1988	Roche et al.	-----	-----	
/	5,986,313	11/16/1999	Ueda et al.	-----	-----	
/	6,458,702	10/1/2002	Aloni	-----	-----	
/	6,656,764	12/2/2003	Wang et al.	-----	-----	
	2002/123222	9/5/2002	Wu	-----	-----	
AKS	2003/230811	12/18/2003	Kim	-----	-----	

## FOREIGN PATENT DOCUMENTS

**OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)**

AICS	<p>"Self-Aligned Technique Employing Planarized Resist For Reducing Poly-Silicon Sheet Resistance By Formation of a Metal Silicide." IBM Technical Disclosure Bulletin, IBM Corp. Vol. 30 No. 5 (1987)</p>

EXAMINER Ashe Kumar Sarhan DATE CONSIDERED 11/30/06

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional)

**Y0R920030334US1 (16899)**

Application Number

**10/786,901**

Applicant(s)

**Ricky S. Amos et al.**

Filing Date

**February 25, 2004**

Group Art Unit

**2891**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		1405 O I P E SEP 19 2005 PATENT & TRADEMARK OFFICE USA					

**U.S. PATENT APPLICATION PUBLICATIONS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AKS		2003/0141565 A1	7/31/2003	Hirose et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS		Oh J. et al. "Interdigitated Ge p-i-n Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers." IEEE Journal of Quantum Electronics, vol. 38, no. 9, (2002)
AKS		Jones R.E. et al. "Fabrication and Modeling of Gigahertz Photodetectors in Heteroepitaxial Ge-on-Si Using a Graded Buffer Layer Deposited by Low Energy Plasma Enhanced CVD." IEDM p793 (2002)

EXAMINER

*As Shekhar Sarbari*

DATE CONSIDERED

*1/30/06*

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.